

## FEATURES

- Dual-Channel SLIC device with small footprint
- Loop start and Ground start support
- +5 V and battery supply required
- Optional dual battery operation
- -39 to -60 V battery operation
- Supplies more than 20 mA into 2000  $\Omega$  from -48 V
- Programmable current limit
- On-chip Thermal Management (TMG) feature in all Active states
- Low standby power (24 mW per channel)
- Supports 2.0 Vrms metering applications
- Control states: Active and Active Metering (Normal and Reverse Polarity), Standby, Tip Open and Disconnect
- 3.3-V compatible to logic control inputs
- Power up in Disconnect state
- On-hook transmission in Active states
- Per-channel fault detection and indication
- Per-channel thermal shutdown
- Programmable Off Hook and Ground Start thresholds.
- Programmable ring-trip detect threshold
- Footprint compatible with Microsemi's Le5711 SLIC

## APPLICATIONS

- Ideal for low-cost, high performance line card applications (CO, DLC)
- Meets requirements for countries such as: India, China, Korea, Japan, Taiwan, and Australia
- Meets requirements for North America DLC applications (TR-57-CORE)

## RELATED LITERATURES

- 081110 Thermal Management for the Le5711 and Le5712 SLIC Devices Application Note
- 080900 Le5711 and Le5712 Comparison Brief Application Note
- 080753 Le58QL02/021/031 QLSLAC™ Data Sheet
- 080754 Le58QL061/063 QLSLAC™ Data Sheet
- 080921 Le58083 Octal SLAC™ Data Sheet
- 080676 Le5711 Dual SLIC Data Sheet

Document ID#: 081047

Version 8

April 2013

## ORDERING INFORMATION

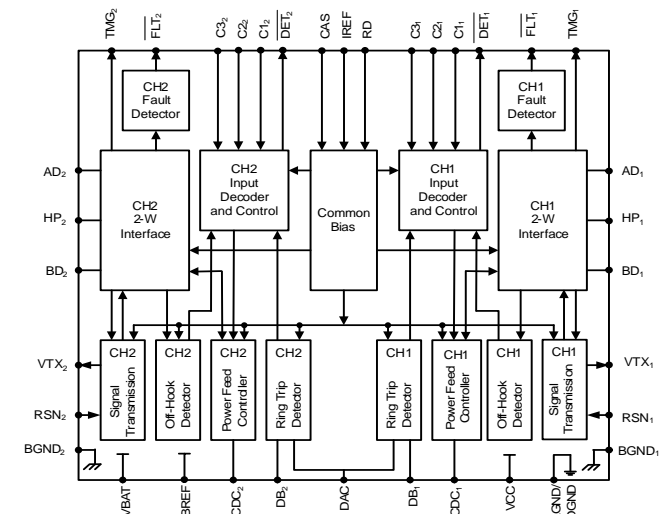
Device	Package Type <sup>1</sup>	Packing <sup>2</sup>
Le57D121BTC	44-pin eTQFP (Green), -53 dB, Reverse Polarity	Tray
Le57D122BTC	44-pin eTQFP (Green), -63 dB, Reverse Polarity	

1. The green package meets RoHS Directive 2002/95/EC of the European Council to minimize the environmental impact of electrical equipment.
2. For delivery using a tape and reel packing system, add a "T" suffix to the OPN (Ordering Part Number) when placing an order.

## DESCRIPTION

The innovative Le5712 dual-channel SLIC device is designed for high-density POTS applications requiring a small-footprint, low-power SLIC device. By combining a fully featured line interface of two channels into one SLIC device, the Le5712 device enables the design of a low-cost, high performance, and fully programmable line interface for multiple country applications worldwide, including Ground Start and metering capability. The on-chip Thermal Management (TMG) feature allows for significantly reduced power dissipation on the device. Optional dual battery operation to reduce total power consumption is also available. The device is offered in a thermally efficient, space-saving 44-pin eTQFP package. The 12 x 12 mm footprint allows designers to make a dramatic increase in the density of lines on a board. The Le5712 device is also designed to significantly reduce the number of external components required for line card design.

## BLOCK DIAGRAM



**TABLE OF CONTENTS**

<b>Features</b> .....	<b>.1</b>
<b>Applications</b> .....	<b>.1</b>
<b>Related Literatures</b> .....	<b>.1</b>
<b>Ordering Information</b> .....	<b>.1</b>
<b>Description</b> .....	<b>.1</b>
<b>Block Diagram</b> .....	<b>.1</b>
<b>Table of Contents</b> .....	<b>.2</b>
<b>Product Description</b> .....	<b>.3</b>
<b>Block Descriptions</b> .....	<b>.3</b>
Two-Wire Interface .....	.3
Signal Transmission .....	.4
Power Feed Controller and Common Bias .....	.4
Input Decoder and Control .....	.5
Device State Decoding .....	.5
Off-Hook Detector (OHD) .....	.5
Ground Start Detector (GSD) .....	.5
Ring-Trip Detector .....	.5
Fault Detector .....	.5
Thermal Shutdown .....	.6
<b>Connection Diagram</b> .....	<b>.6</b>
<b>Pin Descriptions</b> .....	<b>.7</b>
<b>Absolute Maximum Ratings</b> .....	<b>.8</b>
<b>Operating Ranges</b> .....	<b>.8</b>
Environmental Ranges .....	.8
Electrical ranges .....	.8
<b>Electrical Characteristics</b> .....	<b>.9</b>
Summary of Test Conditions .....	.9
Supply Currents and Power Dissipation (on-hook) .....	.9
<b>Specifications</b> .....	<b>.9</b>
Device specifications .....	.9
DC Feed Characteristics .....	.14
Test Circuits .....	.15
<b>POTS Application Circuit (POTS with no metering)</b> .....	<b>.18</b>
<b>Application Circuit Parts List (Pots with no metering)</b> .....	<b>.19</b>
<b>Pulse Metering Application Circuit (Pots with metering)</b> .....	<b>.20</b>
<b>Application Circuit Parts List (Pots with metering)</b> .....	<b>.21</b>
<b>Physical Dimensions</b> .....	<b>.22</b>
<b>Revision History</b> .....	<b>.23</b>
Revision C1 to D1 .....	.23
Revision D1 to E1 .....	.23
Revision E1 to F1 .....	.23
Revision F1 to G1 .....	.23
Revision G1 to G2 .....	.23
Revision G2 (version 7) to Version 8 .....	.23

## PRODUCT DESCRIPTION

The Le5712 device is designed for long loop high-density POTS applications requiring a low power, small footprint SLIC device. The Le5712 device increases line card density by integrating two SLIC devices into a single 44-pin package. This reduction in board space permits a higher density line card, which allows for amortizing common hardware across more channels. The Le5712 device gives line card designers a simple control interface that supports seven states: Active, Active Metering, Reverse Polarity, Reverse Polarity Metering, Standby, Tip Open and Disconnect (Ringing). The low cost and high performance Le5712 device provides the key features for POTS markets requiring loop start, loop start and metering, or ground start. The device includes a thermal management feature for minimizing power dissipation on the SLIC. Alternatively, the device can be operated in a dual battery configuration to reduce overall power consumption.

## BLOCK DESCRIPTIONS

### Two-Wire Interface

The two-wire interface provides DC current and sends voice and signalling information to a customer premise equipment. The two-wire interface also receives the returning signals from the customer premise equipment.

This block implements the thermal management feature, which allows power that would otherwise be dissipated within the package to be off loaded into an external resistor when the line is Off Hook.  $R_{TMGi}$  is connected from  $TMGi$  to the VBAT pin and limits power within the SLIC device (Note: "i" denotes channel number).

The minimum value of  $R_{TMGi}$  is given by:

$$R_{TMGi} \geq \frac{|BAT_{MAX}| - 6 - I_{LIMITMIN} \cdot (2 \cdot R_F + R_{LMIN} + 40\Omega)}{I_{LIMITMIN} - 3 \text{ mA}}$$

where  $I_{LIMITMIN}$  is the minimum programmed loop current limit and  $R_{LMIN}$  is the minimum loop resistance. The tolerance of  $R_{TMGi}$  should be taken into account when selecting a value that meets this requirement. For example, if  $BAT_{MAX} = -56 \text{ V}$ ,  $I_{LOOPMIN} = 30 \text{ mA}$  and  $R_{LMIN} = 200 \Omega$  then  $R_{TMGi} = 1.5 \text{ k}\Omega$  is the minimum recommended value. A value of  $1.8 \text{ k}\Omega$  with 5% accuracy will keep the power in  $R_{TMGi}$  below  $1.0 \text{ W}$ , and the total worst case SLIC power dissipation with both channels active below  $1.6 \text{ W}$ .

The power dissipated in the TMG resistor is given by:

$$P_{RTMG} = \frac{(|BAT| - 5 - I_L \cdot (R_L + 2R_F + 40))^2}{R_{TMG}}$$

where  $I_L$  is the loop current, and  $R_L$  is the loop resistance.

The maximum power on  $R_{TMG}$  is given by:

$$P_{RTMGmax} = \frac{(|BAT|_{max} - 5 - I_{LIMITmin} (R_{Lmin} + 2R_F + 40))^2}{R_{TMGmin}}$$

And the power dissipated per channel in the SLIC device while in the Active states is given by:

$$P_{SLICi} = 0.003|BAT| + (|BAT| - 3 - I_L(R_L + 2R_F + 40)) \left( I_L - \frac{I}{R_{TMG}} (|BAT| - 5 - I_L(R_L + 2R_F + 40)) \right)$$

The maximum power dissipated per channel in the SLIC device while in the Active states is given by:

$$P_{SLICmaxi} = 0.003|BAT|_{max} + \left( 1 + \frac{I_{LIMITmax}}{2} R_{TMGmax} \right) \left( \frac{I_{LIMITmax}}{2} + \frac{1}{R_{TMGmax}} \right)$$

Refer to the *Thermal Management for the Le5711 and Le7512 Dual SLIC Devices Application Note* for further analysis and for dual battery condition.

The AC signal swing supported by the two-wire interface is controlled by the SLIC state. For standard voice transmission, the Active and Reverse Polarity states are used. To support voice plus meter pulses, the Active Metering and Reverse Polarity Metering states are provided which have increased overhead to support  $2.0 \text{ Vrms}$  metering.

## Signal Transmission

The  $RSN_i$  input current controls the receive current sent to the two-wire interface. The AC line voltage is sensed by a differential amplifier between the  $AD_i$  and  $HP_i$  leads. The output of this amplifier is equal to the AC metallic components of the line voltages and is output at  $VTX_i$ .

The desired two-wire AC input impedance,  $Z_{2WIN}$ , is defined by the fuse resistors,  $R_F$ , and an impedance connected from  $VTX_i$  to  $RSN_i$ ,  $Z_{Ti}$ . When computing  $Z_{Ti}$ , the internal current amplifier pole and any external stray capacitance between  $VTX$  and  $RSN$  must be taken into account.

$$Z_{Ti} = \frac{500}{3} \cdot (Z_{2WIN} - 2R_F)$$

To set the desired receive gain ( $G_{42L}$ ) into a load  $Z_L$  from  $VRX_i$ ,  $Z_{RXi}$  is connected from  $VRX_i$  to  $RSN_i$ , where

$$Z_{RXi} = \frac{Z_L}{G_{42L}} \cdot \frac{500 \cdot Z_T}{Z_T + \frac{500}{3}(Z_L + 2R_F)}$$

The transmission block also contains a longitudinal feedback circuit to shunt longitudinal signals to a DC bias voltage. The longitudinal feedback does not affect metallic signals.

Two application circuits, provided at the end of this data sheet, show how the Le5712 device can connect directly to pins of a QLSLAC codec.

The [POTS Application Circuit \(POTS with no metering\), on page 18](#) shows an application providing Loop Start and Ground Start capability. The components selected for the transmission network allow a wide range of market transmission requirements to be met when combined with the programmable QLSLAC device. In addition, transmit relative levels of  $L_i = +4$  to  $-4$  dB and receive relative levels of  $L_o = 0$  to  $-8$  dB can be supported using only the digital gain within the QLSLAC device for all markets. This configuration will meet ITU Q.552 and GR57 requirements.

The [Pulse Metering Application Circuit \(Pots with metering\), on page 20](#) shows a configuration for use in a 12 or 16 kHz pulse metering application with the QLSLAC device. The design allows 2 V<sub>rms</sub> into 200  $\Omega$ , and supports gain ranges of at least  $L_i = 0$  to  $+4$  dB, and  $L_o = 0$  to  $-8$  dB. This configuration will meet ITU Q.552 requirements over these gain ranges for markets such as India and China.

The relationship between metering source  $V_M$ , the feeding resistance,  $R_M$ , and the output voltage at tip-ring,  $V_{TR}$ , is given in the following equation. The load at tip-ring is  $R_M$ .  $R_F$  is the protection and other, if any, front-end resistances.  $Z_T$  is the impedance between  $VTX$  and  $RSN$  at metering frequency.

$$V_{TR} = \frac{Z_M}{R_M} \cdot \frac{500}{1 + \frac{500}{3} \cdot \frac{Z_M + 2R_F}{Z_T}} V_M$$

Metering signal at  $VTX$  needs to be filtered to prevent from overloading the codec. This has been realized in the applications circuitry in this document.

## Power Feed Controller and Common Bias

The power feed controllers have three sections: (1) the common bias circuit, (2) the battery feed circuit, and (3) the reverse polarity circuit which operate in all Active states.

The bias circuit provides a signal which sets the current limit and creates a voltage related to  $V_{BAT}$ , filtered by a capacitor connected to the CAS pin, to the battery feed circuit.

The nominal current limit is set by the following equation:  $I_{LIMIT} = \frac{470}{R_{REF}}$

A recommended 3 Hz filter pole frequency ( $f_c$ ) can be implemented from:  $C_{CAS} = \frac{1}{RI_{AS} \cdot 2 \cdot \pi \cdot f_c}$

The battery feed circuit regulates the amount of DC current and voltage supplied to the telephone over a wide range of loop resistance. It is designed to operate over a nominal 22 to 33 mA range of programmed current limit. It produces a filtered reference voltage offset from the subscriber line voltage which is applied to the two-wire interface.

In addition, a low pass filter is implemented with a capacitor connected to the  $CDC_i$  pin.

In the low power Standby state, an alternative feed is implemented via two current limited on chip 200- $\Omega$  resistors. The nominal loop current below current limit in the Standby state is given by:

$$I_{STANDBY} = \frac{|V_{BAT}| - 4 \text{ V}}{600 \Omega + R_L}$$

## Input Decoder and Control

The input decoder and control block provides a means for a microprocessor or SLAC device IC to control such system states as Active, Active Metering, Reverse Polarity, Reverse Polarity Metering, Standby, Tip Open and Disconnect (Ringing). The input decoder and control block has TTL-compatible inputs, permitting interfacing to 5 or 3.3 V VCC controllers which set the operating states of the SLIC device. It also provides the loop supervision signal sent back to the controller.

From power up, the device is in disconnect state unless over-written by external control inputs.

## Device State Decoding

(For channel  $i = 1$  or  $2$ )

State	C3 <sub>i</sub>	C2 <sub>i</sub>	C1 <sub>i</sub>	Two-Wire state	$\overline{\text{DET}}_i$ output
0	0	0	0	Reserved	N/A
1	0	0	1	Active Metering	OHD
2	0	1	0	Tip Open	GSD
3	0	1	1	Reverse Polarity Metering	OHD
4	1	0	0	Disconnect	RTD
5	1	0	1	Active	OHD
6	1	1	0	Standby	OHD
7	1	1	1	Reverse Polarity	OHD

## Off-Hook Detector (OHD)

The On-to-Off-hook and Off-to-On-hook detections are based on loop current and are defined as  $|I_{AD} - I_{BD}| / 2$ . The On-to-Off-hook (OHD) and Off-to-On-hook (OND) thresholds are programmed with the  $R_D$  resistor and the threshold applies to all Active and Standby states.

$$I_{\text{OHD}} = \frac{935\text{V}}{R_D}$$

$$I_{\text{OHD}} = I_{\text{OND}} + \text{Hysteresis}$$

Upon the loss of battery the  $\overline{\text{DET}}$  pin will be HIGH.

Off-hook detection or  $\overline{\text{DET}}$  state should be ignored during on-hook metering.

## Ground Start Detector (GSD)

This detector is active in the Tip Open state. The threshold,  $I_{\text{GSD}}$ , is defined by the same equation used for the OHD.

For ground start lines, the device is in the Tip Open state between calls. When a ring ground condition is detected, the device should be switched to the Active state. During this period, the  $\overline{\text{DET}}$  pin will be active if the ring to ground current is greater than twice the  $I_{\text{OHD}}$  threshold. The  $\overline{\text{DET}}$  pin will go active once the ring ground is removed and a loop is applied. It is recommended that a firmware time-out period is applied in case the call attempt is abandoned and  $\overline{\text{DET}}$  never goes low. The time-out is reset once an active  $\overline{\text{DET}}$  is seen in the Active state.

## Ring-Trip Detector

In the Disconnect state, the ring-trip detector is active. While the  $\text{DB}_i$  pin is more negative than the DAC pin, the  $\overline{\text{DET}}$  pin will be High to indicate on hook. When an off hook condition occurs, the  $\text{DB}_i$  pin becomes more positive than the DAC pin, and the  $\overline{\text{DET}}$  pin will go Low to indicate off hook during ringing (ring-trip) has been detected. The system implements the Ringing state using external control of a ring relay in combination with the Disconnect SLIC device state, which enables the ring-trip detector.

The [POTS Application Circuit \(POTS with no metering\), on page 18](#) shows a ring trip bridge configured and components are selected for a typical battery-backed ringing applications such as for the US (TR-57) and China (GF002).

The [Pulse Metering Application Circuit \(Pots with metering\), on page 20](#) shows a ring trip bridge configured and components are selected for a typical earth-backed ringing applications such as in India (G/LLT and G/MLT).

## Fault Detector

The DSLIC device provides a fault detection function in the Active states on each channel. Under a fault condition the detector senses longitudinal voltage at tip and ring and flags a fault by pulling the  $\overline{\text{FLT}}_i$  pin Low. The  $\overline{\text{FLT}}_i$  pins are compatible with logic outputs, and may be monitored to clearly identify a fault condition from a loop condition.

In case of low level longitudinal AC induction the  $\overline{\text{FLT}}_i$  may pulse at twice the frequency of the induction signal.

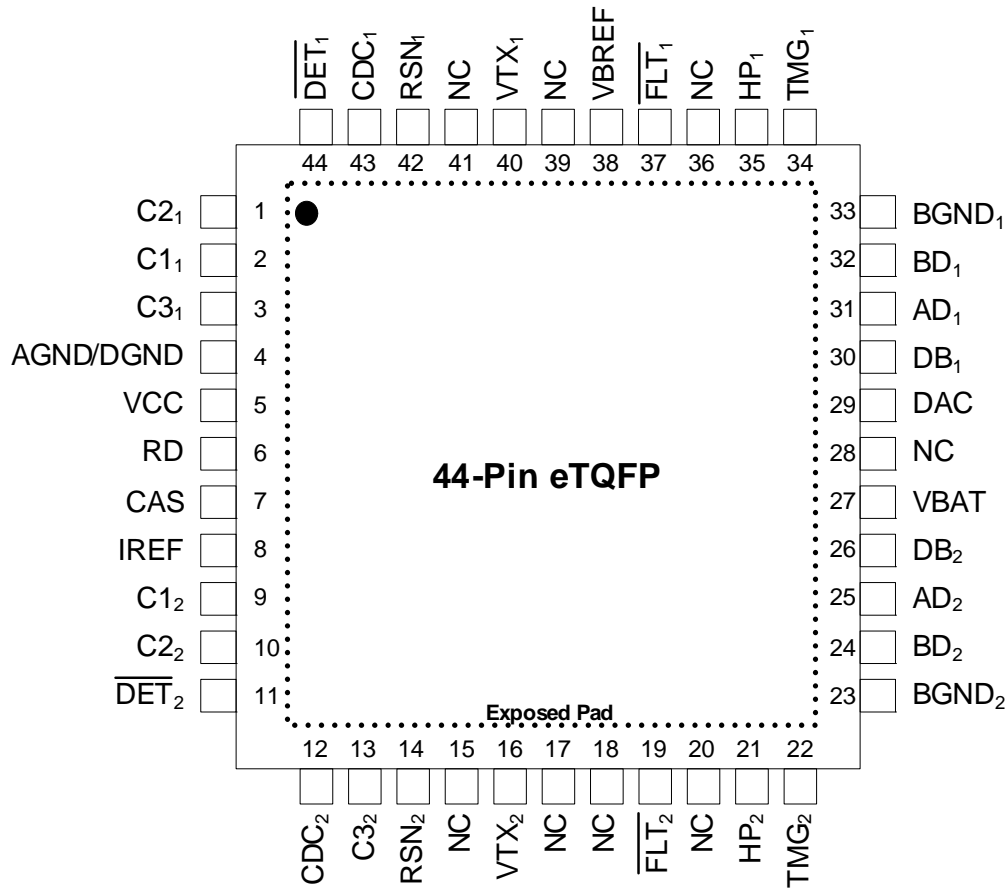
Upon the loss of battery the  $\overline{\text{FLT}}$  pin will be LOW.

## Thermal Shutdown.

Thermal shutdown is provided on a per channel basis to protect the die from excessive temperature. Persistent faults will produce high power dissipation, and may result in the affected channel triggering its thermal shutdown detector (Minimum > 145° C). At this point the power amplifiers are turned off and the device is in a disconnect like state,  $\overline{FLT}$  and  $\overline{DET}$  will be active. The thermal shutdown detector has approximately 10° C of hysteresis. Thermal shutdown on one channel will not affect the operation of the other channel.

The thermal performance of a thermally enhanced package is assured through optimized printed circuit board layout. The thermal pad at the bottom of the package should be soldered down to printed circuit board. Refer to the *Thermal Management for the Le5711 and Le7512 Dual SLIC Devices Application Note* for details.

## CONNECTION DIAGRAM



**Note:**

1. Pin 1 is marked for orientation.
2. NC = No Connect
3. The exposed heat sink pad on the bottom of the eTQFP package should be connected to VBAT pin - the SLIC side of the diode from battery supply. Do not connect it to GND.

## PIN DESCRIPTIONS

Pin Name	Type	Description
AD <sub>1</sub>	Output	Output of AD power amplifier of channel 1.
AD <sub>2</sub>	Output	Output of AD power amplifier of channel 2.
AGND/DGND	Ground	Analog and digital ground.
BD <sub>1</sub>	Output	Output of BD power amplifier of channel 1.
BD <sub>2</sub>	Output	Output of BD power amplifier of channel 2.
BGND <sub>1</sub>	Ground	Battery (power) ground of channel 1
BGND <sub>2</sub>	Ground	Battery (power) ground of channel 2.
C <sub>1</sub> /C <sub>2</sub> /C <sub>3</sub> <sub>1</sub>	Input	State decoder inputs of channel 1.
C <sub>1</sub> /C <sub>2</sub> /C <sub>3</sub> <sub>2</sub>	Input	State decoder inputs of channel 2.
CAS	Capacitor	Pin for capacitor to filter reference voltage when operating in anti-saturation region.
CDC <sub>1</sub>	Capacitor	DC feed filter capacitor of channel 1.
CDC <sub>2</sub>	Capacitor	DC feed filter capacitor of channel 2.
$\overline{\text{FLT}}_1$	Output	Channel 1 fault detector output <sup>1</sup> .
$\overline{\text{FLT}}_2$	Output	Channel 2 fault detector output <sup>1</sup> .
DAC	Input	Ring-trip negative of both channels. Negative input to ring-trip comparator.
DB <sub>1</sub>	Input	Ring-trip positive of channel 1. Positive input to ring-trip comparator.
DB <sub>2</sub>	Input	Ring-trip positive of channel 2. Positive input to ring-trip comparator.
DET <sub>1</sub>	Output	Off Hook / Ring-trip detector output of channel 1. Logic low indicates that a detector is tripped.
DET <sub>2</sub>	Output	Off Hook / Ring-trip detector output of channel 2. Logic low indicates that a detector is tripped.
HP <sub>1</sub>	Capacitor	Connect a High-Pass filter capacitor in series with a resistor from HP <sub>1</sub> to BD <sub>1</sub> .
HP <sub>2</sub>	Capacitor	Connect a High-Pass filter capacitor in series with a resistor from HP <sub>2</sub> to BD <sub>2</sub> .
IREF	Resistor	Connection for reference resistor that programs Off Hook Detector threshold and DC feed current limit of both channels.
NC	—	No Connect. This pin is not internally connected.
RD	Resistor	Connection for resistor that programs off hook detector threshold of both channels.
RSN <sub>1</sub>	Input	Receive Summing Node of channel 1. In the Active and Reverse Polarity states, the current (both AC and DC) between AD <sub>1</sub> and BD <sub>1</sub> is equal to 500 times the current into this pin. The networks that program receive gain, metering gain and two-wire impedance of Channel 1 connect to this node.
RSN <sub>2</sub>	Input	Receive Summing Node of channel 2. In the Active and Reverse Polarity states, the current (both AC and DC) between AD <sub>2</sub> and BD <sub>2</sub> is equal to 500 times the current into this pin. The networks that program receive gain, metering gain and two-wire impedance of Channel 2 connect to this node.
TMG <sub>1</sub>	Output	Thermal management of channel 1. External resistor connects from TMG <sub>1</sub> to VBAT to off-load power from the SLIC device.
TMG <sub>2</sub>	Output	Thermal management of channel 2. External resistor connects from TMG <sub>2</sub> to VBAT to off-load power from the SLIC device.
VBAT	Battery	Battery supply and connection to substrate. Connect to highest negative supply with a diode on a per line base.
VBREF	Input	This is a Microsemi reserved pin and must always be connected to the VBAT pin.
VCC	Power	+5 V power supply.
VTX <sub>1</sub>	Output	Transmit audio signal of channel 1. This output is a scaled version of the A and B metallic voltage. VTX <sub>1</sub> also sources the two-wire input impedance programming network.
VTX <sub>2</sub>	Output	Transmit audio signal of channel 2. This output is a scaled version of the A and B metallic voltage. VTX <sub>2</sub> also sources the two-wire input impedance programming network.
EPAD	Battery	The exposed heat sink pad on the bottom of the eTQFP package should be connected to VBAT pin - the SLIC side of the diode from battery supply. This thermal pad should also be soldered down to printed circuit board to achieve the desired package thermal performance.

## Note:

1. Consult Microsemi representatives for proper handling when not in use.

## ABSOLUTE MAXIMUM RATINGS

Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods can affect device reliability

Storage temperature	-55 to +150° C
V <sub>CC</sub> with respect to AGND / DGND	-0.4 to +7.0 V
V <sub>BAT</sub> with respect to AGND / DGND	+0.4 to -63 V
BGND <sub>1</sub> , BGND <sub>2</sub> with respect to AGND / DGND	+3 to -3 V
AD <sub>1</sub> , AD <sub>2</sub> , BD <sub>1</sub> , BD <sub>2</sub> with respect to BGND:	
Continuous	V <sub>BAT</sub> to +1 V
10 ms (F = 0.1 Hz)	-70 to +5 V
1 μs (F = 0.1 Hz)	-80 to +8 V
250 ns (F = 0.1 Hz)	-90 to +12 V
Current from AD <sub>1</sub> , AD <sub>2</sub> , BD <sub>1</sub> , BD <sub>2</sub>	±150 mA
DB <sub>1</sub> , DB <sub>2</sub> , and DAC inputs:	
Voltage on ring-trip inputs	V <sub>BAT</sub> to 0 V
Current into ring-trip inputs	±10 mA
C1 <sub>1</sub> , C2 <sub>1</sub> , C3 <sub>1</sub> , C1 <sub>2</sub> , C2 <sub>2</sub> , C3 <sub>2</sub>	
Input Voltage	-0.4 to V <sub>CC</sub> + 0.4 V
Maximum power dissipation in 44-pin eTQFP	
T <sub>A</sub> = 70° C, continuous	(see note 1)
Thermal Data in 44-pin eTQFP package	
Junction to Ambient, θ <sub>JA</sub>	(see note 2)
ESD Immunity (Human Body Model)	JESD22 Class 1C compliant

### Notes:

1. Thermal limiting circuitry on chip will shut down the circuit at a junction temperature of about 165° C. Continuous operation above 145° C junction temperature may degrade device reliability. Refer to the *Thermal Management for the Le5711 and Le7512 Dual SLIC Devices Application Note* for details.
2. The thermal performance of a thermally enhanced package is assured through optimized printed circuit board layout. Refer to the *Thermal Management for the Le5711 and Le7512 Dual SLIC Devices Application Note* for details.

## Package Assembly

Green package devices are assembled with enhanced, environmental compatible lead-free, halogen-free, and antimony-free materials. The leads possess a matte-tin plating which is compatible with conventional board assembly processes or newer lead-free board assembly processes. The peak soldering temperature should not exceed 245°C during printed circuit board assembly.

Refer to IPC/JEDEC J-Std-020B Table 5-2 for the recommended solder reflow temperature profile.

## OPERATING RANGES

The operating ranges specified below define those limits between which the device operates and is guaranteed under the noted test conditions. (Refer to [Summary of Test Conditions, on page 9.](#))

## Environmental Ranges

Microsemi guarantees the performance of this device over commercial (0 to 70° C) and industrial (-40 to 85° C) temperature ranges by conducting electrical characterization, production testing, and periodic sampling over each range. These characterization and test procedures comply with section 4.6.2 of Bellcore GR-357-CORE Component Reliability Assurance Requirements for Telecommunications Equipment.

Ambient Temperature	-40° to 85°C
Ambient Relative Humidity	15% to 85%

## Electrical ranges

V <sub>CC</sub>	4.75 to 5.25 V
V <sub>BAT</sub>	-39 to -60 V
DB <sub>1</sub> , DB <sub>2</sub> , and DAC	V <sub>BAT</sub> to -2 V
AGND	0 V
BGND <sub>1</sub> , BGND <sub>2</sub> with respect to AGND/DGND	-100 to +100 mV
Load resistance on VTX <sub>1</sub> , VTX <sub>2</sub> to ground	8 kΩ minimum



## ELECTRICAL CHARACTERISTICS

### Summary of Test Conditions

Unless otherwise noted, the test conditions are defined by the Le5712 device test circuit shown in [Figure 7, on page 17](#) with:  $V_{CC}=5\text{ V}$ ,  $BAT = -52\text{ V}$ ,  $R_L = R_{LAC} = 600\ \Omega$ ,  $R_{REF} = 14.3\text{ k}\Omega$ ,  $R_D = 82.5\text{ k}\Omega$ .

### Supply Currents and Power Dissipation (on-hook)

Operational State	$I_{CC}$ mA (Note 1.)			$I_{VBAT}$ mA (Note 1.)			SLIC Device Power mW			Note
	Min.	Typ	Max	Min.	Typ	Max	Min.	Typ	Max	
Disconnect		3.2	5.5		0.5	0.8		42	62	
Standby		3.2	6.5		0.6	1.0		46	70	
Tip Open		3.1	6.5		0.6	1.0		46	70	
Active		9.0	13		6.0	10.0		353	540	
Reverse Polarity		9.0	13		6.0	10.0		353	540	
Active Metering		9.3	13		6.0	10.0		355	540	2
Reverse Polarity Metering		9.3	13		6.0	10.0		355	540	
One channel Standby One channel Active		6.1	10		3.3	5.5		200	305	

## SPECIFICATIONS

### Device specifications

Specification	Condition	Min.	Typ	Max	Unit	Note
<b>Line Characteristics</b>						
VAB, Open Circuit	Active Forward	42.75	45.7	48	V	
	Active Reverse	42.5				
	Standby	46.75	52			
	Metering Forward Metering Reverse	38 37.5	41.5 42.5			
$I_L$ , Long Loops, Active state	$R_{LDC} = 2000\ \Omega$ , $BAT = -48\text{ V}$	19.8	20.5		mA	
$I_{LIMIT}$ , Short Loops, Active state	$R_{LDC} = 100\ \Omega$ to $1100\ \Omega$	30	33	36	mA	3
$I_L$ , Long Loops, Active state	$R_{LDC} = 2125\ \Omega$	20	21.1		mA	
$I_L$ , Long Loops, Active state	$R_{LDC} = 2125\ \Omega$ , $BAT = -46.5\text{ V}$	18	18.5		mA	
$I_L$ , Accuracy, Standby state	$I_L = \left( \frac{ BAT -4V}{(R_L + 600)} \right)$ , $R_{LDC} \geq 2000\ \Omega$	$0.9I_L$	$I_L$	$1.1I_L$	mA	
	Current Limited Region	20	30	45		
$I_{LIM}$ , AD and BD to BGND	Active, $I_{AD} + I_{BD}$		85	120	mA	
$I_L$ , Loop current, Disconnect state	$R_L = 0\ \Omega$			100	$\mu\text{A}$	
$I_{AD}$ leakage, Tip Open state	$R_L = 0\ \Omega$			100	$\mu\text{A}$	
$I_{BD}$ current, Tip Open state	BD to BGND	20	30	45	mA	
$V_{AD}$ Active and Standby states	AD to $BAT=7\text{ k}\Omega$ , BD to $GND=100\ \Omega$	-7.5	-5		V	
$V_{REF}$ , IREF pin output voltage		1.2	1.25	1.3	V	
K1, Incremental RSN current gain		490	500	510	A/A	
<b>Power Supply Rejection Ratio at the Two-Wire Interface (Active states, On or Off Hook)</b>						
$V_{CC}$	50 Hz to 3.4 kHz $V_{RIPPLE} = 100\text{ mVrms}$	30	40		dB	4
	$V_{BAT}$	$V_{RIPPLE} = 100\text{ mVrms}$ 300 Hz to 3.4 kHz	28	50		
		50 Hz to 60 Hz	20			
$R_{IAS}$ , Effective internal resistance	CAS pin to AGND	90	150	210	k $\Omega$	2

Specification	Condition	Min.	Typ	Max	Unit	Note
<b>Longitudinal Capability (See <a href="#">Figure 4, on page 16.</a>)</b>						
Longitudinal to metallic L-T balance 200 Hz to 1.0 kHz, Le57122	Normal polarity 0° C to +70° C	-60	-64		dB	
Longitudinal to metallic L-T balance 3.0 kHz, Le57122	Normal polarity 0° C to +70° C	-57	-61		dB	
Longitudinal to metallic L-T balance 200 Hz to 1.0 kHz, Le57122	Normal polarity -40° C to +85° C	-57	-64		dB	2
Longitudinal to metallic L-T balance 3.0 kHz, Le57122	Normal polarity -40° C to +85° C	-54	-61		dB	2
Longitudinal to metallic L-T balance 200 Hz to 3.0 kHz, Le57121	0° C to +70° C	-53			dB	
Longitudinal to metallic L-T balance 200 Hz to 3.0 kHz, Le57121	-40° C to +85° C	-50				2
Longitudinal signal generation 4-L	200 Hz to 3.4 kHz	40			dB	
Longitudinal current per pin (AD <sub>i</sub> or BD <sub>i</sub> )	Active state (off hook)	8.5			mArms	5
Longitudinal impedance at AD <sub>i</sub> or BD <sub>i</sub>	0 to 100 Hz		18.5		Ω /pin	
<b>RFI Rejection (See <a href="#">Figure 6, on page 16.</a>)</b>						
VTX <sub>1</sub> or VTX <sub>2</sub>	f = .01 to 100 MHz HF gen. output = 1.5 Vrms C <sub>AXi</sub> = C <sub>BXi</sub> = 33 nF C <sub>AXi</sub> = C <sub>BXi</sub> = 2.2 nF				1 3 mVrms	2
<b>Transmission Performance</b>						
2-wire return loss	200 Hz to 3.4 kHz (See <a href="#">Figure 5, on page 16</a> )	26			dB	2, 6
Analog output (VTX) impedance			3	25	Ω	2
Analog (VTX) output offset voltage		-50		+50	mV	
Overload level, 2-wire	Active or Reverse Polarity state	2.5			Vpk	7
Overload level, 2-wire	On hook, Active or Reverse Polarity state	1.1				8
Overload level, 2-wire	Metering states	5.5				7
Overload level, 2-wire	On hook, Metering states	5.5				8
THD (Total Harmonic Distortion)	0 dBm		-64	-50	dB	4
	+7 dBm		-55	-40		
	+9 dBm, Metering states		-55	-40		
THD, On hook	0 dBm, R <sub>LAC</sub> = 600 Ω			-36		
THD with metering	R <sub>L</sub> = 300 Ω			-35		2, 9
Idle Channel Noise	C-Message, R <sub>L</sub> = 600 Ω		7	12	dBmC	2
	Psophometric, R <sub>L</sub> = 600 Ω		-83	-78	dBmp	2, 10
Idle Channel Noise with Metering	Psophometric, R <sub>L</sub> = 300 Ω, Metering states			-46		
<b>Crosstalk Between Channels</b>						
Crosstalk coupling loss	Averaged over 200 Hz to 3.4 kHz, 0dBm		80		dB	11

Specification	Condition	Min.	Typ	Max	Unit	Note
<b>Insertion Loss</b> (See <a href="#">Figure 2</a> and <a href="#">Figure 3, on page 15.</a> )						
Gain, 4-to-2-wire	0 dBm, 1 kHz	-0.25	0	+0.20	dB	2
Gain $K_{TX}$ , 2-to-4-wire	0 dBm, 1 kHz	-9.74	-9.54	-9.32		
Gain, 4-to-4-wire	0 dBm, 1 kHz	-9.74	-9.54	-9.34		
Gain, 4-to-2-wire	On hook	-0.35		+0.35		
Gain over frequency	300 to 3400 Hz, relative to 1 kHz	-0.15		+0.15		
Gain tracking	+3 to -55 dBm, relative to 0 dBm	-0.15		+0.15		
Gain tracking, On hook	0 dBm to -37 dBm +3 dBm to 0 dBm	-0.15 -0.35		+0.15 +0.35		
Metering Gain, 4-to-2-wire	$V_M = 0.5$ vrms, 16 kHz, $R_L = 300 \Omega$	15.1	15.6	16.1	dB	12
<b>Logic Interface</b>						
<b>Inputs (<math>C1_1</math>, <math>C1_2</math>, <math>C2_1</math>, <math>C2_2</math>, <math>C3_1</math> and <math>C3_2</math>)</b>						
$V_{IH}$ , Input High voltage		2.0			V	
$V_{IL}$ , Input Low voltage				0.8		
$I_{IH}$ , Input High current	$V_{IH}=2.0V$	-110		90	$\mu A$	
$I_{IL}$ , Input Low current	$V_{IL}=0.8V$	-400				
<b>Outputs (<math>DET_1</math> and <math>DET_2</math>)</b>						
$V_{OL}$ , Output Low voltage	$I_{OUT} = 0.3$ mA			0.40	V	
$V_{OH}$ , Output High voltage	$I_{OUT} = -0.1$ mA	2.4				
<b>Outputs (<math>FLT_1</math> and <math>FLT_2</math>)</b>						
$V_{OL}$ , Output Low voltage	$I_{OUT} = 0.06$ mA			0.40	V	
$V_{OH}$ , Output High voltage	$I_{OUT} = -0.01$ mA	2.4				
<b>Ring-Trip Detector Input (Applies to DAC, <math>DB_1</math> and <math>DB_2</math>.)</b>						
Bias Current		-50	-10	0	nA	2
Offset voltage	Source resistance = 2 M $\Omega$	-50	0	+50	mV	13
Common Mode Voltage Range		$V_{BAT} + 1$		-2	V	2
<b>Fault Detector (See <a href="#">Figure 1, on page 15.</a>)</b>						
$I_{FAULT} =  I_{AD} + I_{BD} $		8	11.5	22	mA	
<b>Off-Hook and Ground Start Detectors (See <a href="#">Figure 1, on page 15.</a>)</b>						
$I_{OHD}$ On-to-Off hook Detection Threshold	Active and Standby states	9.8	11.5	13.2	mA	
Hysteresis	The difference between On-to-Off hook detection threshold and Off-to-On hook Detection threshold	1.3	2.0	2.7		
$I_{GSD}$ , Ground Start Detect threshold (On-to-Off hook detection threshold)	Tip Open state	11.8	13.5	16.0		
Hysteresis (Ground Start)	The difference between On-to-Off hook detection threshold and Off-to-On hook detection threshold	2.6	4.0	5.4		

## Notes:

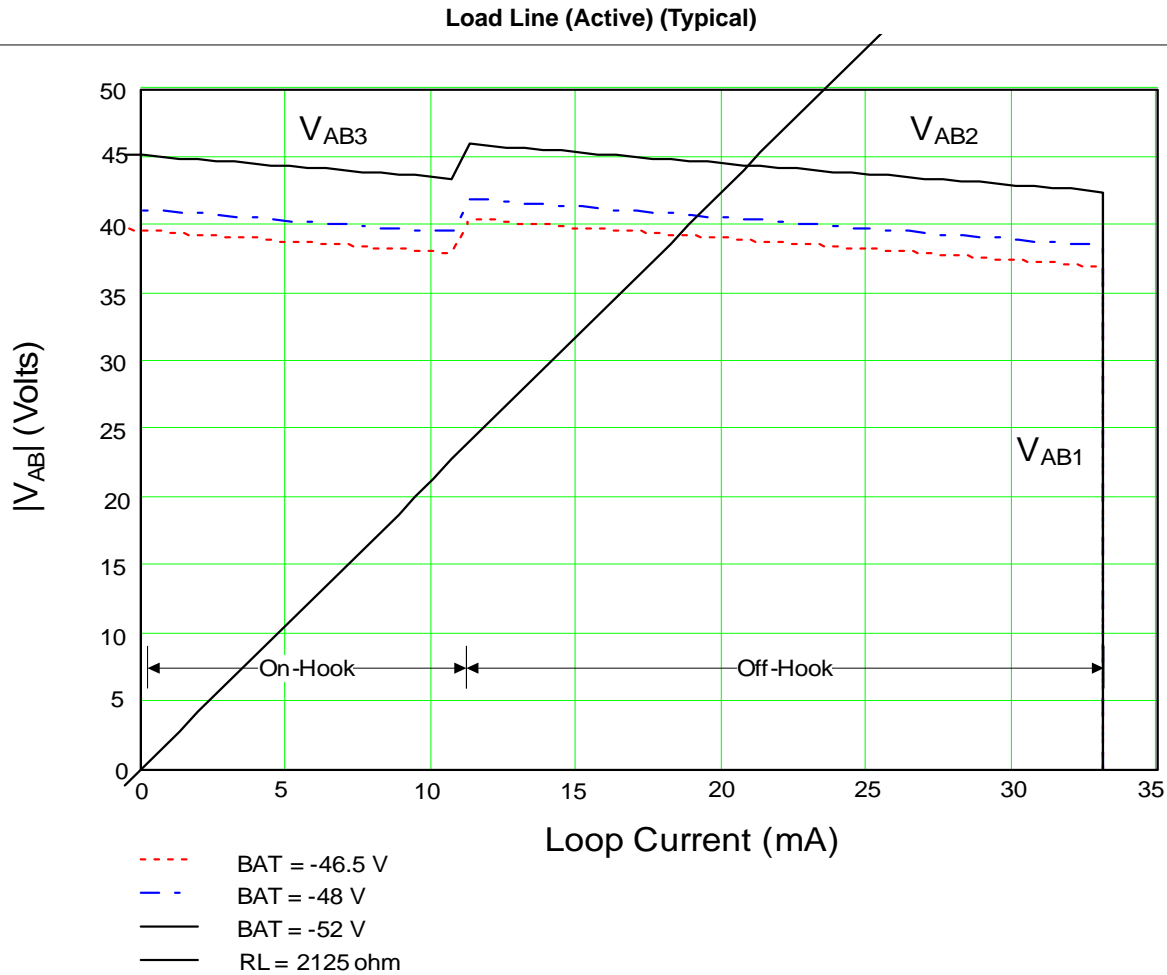
1. Total current measured with both channels in the same state, unless otherwise specified.
2. Not tested in production. This parameter is guaranteed by characterization or correlation to other tests.
3. Typical current limit range is designed to be between 22 mA and 33 mA.
4. This parameter is tested at 1 kHz in production. Performance at other frequencies is guaranteed by characterization.
5. Minimum current level guaranteed not to cause a false loop detect. The fault detector may activate with longitudinal currents above 2.8 mA rms, and may pulse at twice the frequency of the interfering signal.
6. Group delay can be greatly reduced by using a  $Z_T$  network such as that shown in [Figure 5, on page 16](#) where  $C_T = 120$  pF,  $R_{TA} = R_{TB} = 50$  k $\Omega$ . The network reduces the group delay to less than 2  $\mu$ s and increases 2WRL. The effect of group delay on line card performance also may be compensated by synthesizing complex impedance with the QLSLAC™ or Octal SLAC™ devices.
7. Overload level is defined as THD = 1%.
8. Overload level is defined as THD = 1.5%.
9. Total Harmonic distortion with metering is specified with a metering signal of 3.0 Vrms at the two-wire output, and a transmit signal of +3 dBm or receive signal of -4 dBm. The transmit or receive signals are single frequency inputs, and the distortion is measured as the highest in band harmonic at the two-wire or the four-wire output relative to the input signal.
10. Noise with metering is measured by applying a 3.0 Vrms metering signal (measured at the two-wire output) and measuring the psophometric noise at the two-wire outputs over a 200 ms time interval
11. This is test at 1 kHz in production
12. In the test set up,  $Z_T = 100$  k $\Omega$ ,  $R_M = 16.5$  k $\Omega$ , and  $R_F = 0$   $\Omega$ . The output voltage at tip/ring is expected to be 3 Vrms, into a load of 300  $\Omega$ , with 0.5 Vrms source. The typical gain is 15.6 dB.
13. Tested with 0  $\Omega$  source impedance. 2 M $\Omega$  is specified for system design only.

## User-Programmable Components Summary

Equation	Description
$Z_{Ti} = \frac{500}{3}(Z_{2WIN} - 2R_F)$	$Z_{Ti}^*$ is connected between the VTX and RSN pins. The fuse resistors are $R_F$ , and $Z_{2WIN}$ is the desired 2-wire AC input impedance. When computing $Z_{Ti}$ , the internal current amplifier pole and any external stray capacitance between VTX and RSN must be taken into account.
$Z_{RXi} = \frac{Z_L}{G_{42L}} \cdot \frac{500 \cdot Z_T}{Z_T + \frac{500}{3} \cdot (Z_L + 2R_F)}$	$Z_{RXi}^*$ is connected from VRX to RSN. $Z_{Ti}$ is defined above, and $G_{42L}$ is the desired receive gain.
$R_{REF} = \frac{470 \cdot V}{I_{LIMIT}}$	$I_{LIMIT}$ is the desired loop current limit in the constant-current region.
$C_{CAS} = \frac{1}{R_{IAS} \cdot 2\pi \cdot f_c}$	$C_{CAS}$ is the regulator filter capacitor and $f_c$ is the desired filter cut-off frequency.
$I_{OHD} = I_{GSD} = \frac{935 \cdot V}{R_D}$	Off Hook Detect ( $I_{OHD}$ ) and Ground Start Detect ( $I_{GSD}$ ) thresholds are typically set at 10 to 12 mA.
$I_{STANDBY} = \frac{ V_{BAT}  - 4 V}{600 \Omega + R_L}$	Standby loop current (resistive region).
<b>Thermal Management Equations (All Active states for one channel) (Please refer to the <i>Thermal Management for the Le5711 and Le7512 Dual SLIC Devices</i> Application Note for details about dual battery operation.)</b>	
$R_{TMG} \geq \frac{ BAT_{MAX}  - 6 - I_{LIMITMIN} \cdot (2 \cdot R_F + R_{LMIN} + 40\Omega)}{I_{LIMITMIN} - 3 \text{ mA}}$	$R_{TMG}$ is connected from TMG to VBAT and limits power within the SLIC device in Active, Off-Hook states.
$P_{RTMGmax} = \frac{( BAT _{max} - 5 - I_{LIMITmin}(R_{Lmin} + 2R_F + 40))^2}{R_{TMGmin}}$	Maximum power dissipated in the TMG resistor, $R_{TMG}$ , during Active, Off-Hook states.
$P_{SLICmaxi} = 0.003 BAT _{max} + \left(1 + \frac{I_{LIMITmax}}{2} R_{TMGmax}\right) \left(\frac{I_{LIMITmax}}{2} + \frac{1}{R_{TMGmax}}\right)$	Maximum power dissipated per channel in the SLIC device while in Active, Off-Hook states.

\* "i" denotes channel number

## DC Feed Characteristics

**Regions:**

1. Constant current region:

$$V_{AB1} = I_{LOOP} R_L = \frac{470}{R_{REF}} R_L, \text{ where, } R_L = R_L' + 2R_F$$

In Active and Reverse Polarity states

2. Battery tracking anti-sat (Off-hook):

$$V_{AB2} = |BAT| - 7 \text{ V} + \frac{47 \cdot \text{k}\Omega \cdot \text{V}}{R_{REF}} - I_L \cdot 160 \text{ }\Omega$$

3. Battery tracking anti-sat (On-hook):

$$V_{AB3} = |BAT| - 7 \text{ V} + \frac{10 \cdot \text{k}\Omega \cdot \text{V}}{R_{REF}} - I_L \cdot 160 \text{ }\Omega$$

In Active Metering and Reverse Polarity Metering states

4. Battery tracking anti-sat (Off-hook):

$$V_{AB2} = |BAT| - 10.7 \text{ V} + \frac{47 \cdot \text{k}\Omega \cdot \text{V}}{R_{REF}} - I_L \cdot 160 \text{ }\Omega$$

5. Battery tracking anti-sat (On-hook):

$$V_{AB3} = |BAT| - 10.7 \text{ V} + \frac{10 \cdot \text{k}\Omega \cdot \text{V}}{R_{REF}} - I_L \cdot 160 \text{ }\Omega$$

Test Circuits

Figure 1. Feed Programming

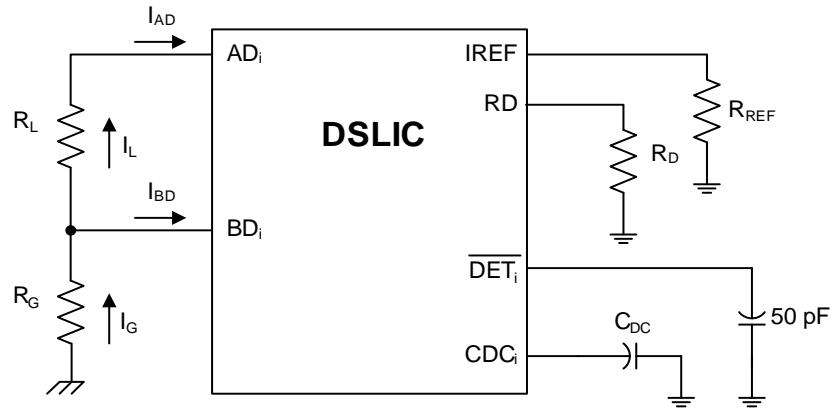


Figure 2. Two-to-Four Wire Insertion Loss

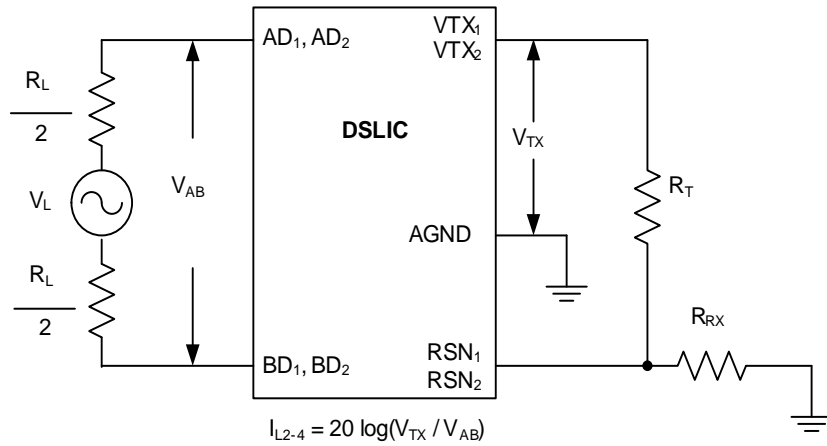


Figure 3. Four-to-Two Wire Insertion Loss and Balance Return Signals

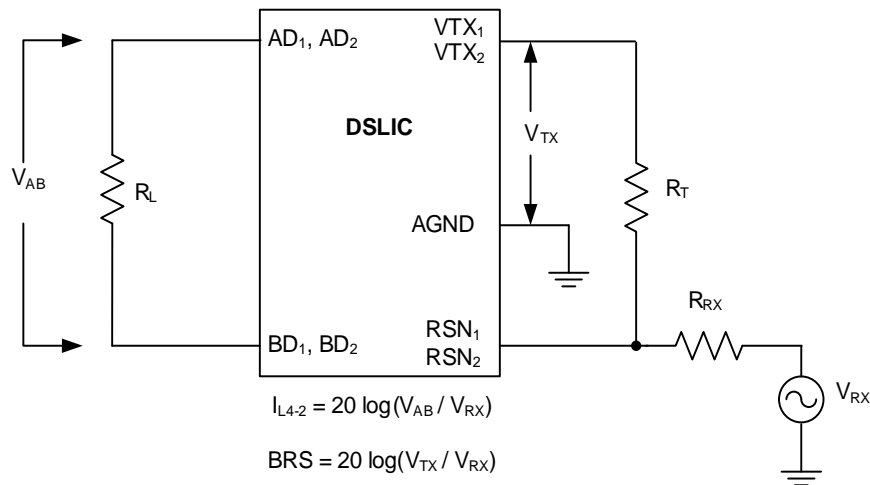


Figure 4. Longitudinal Balance

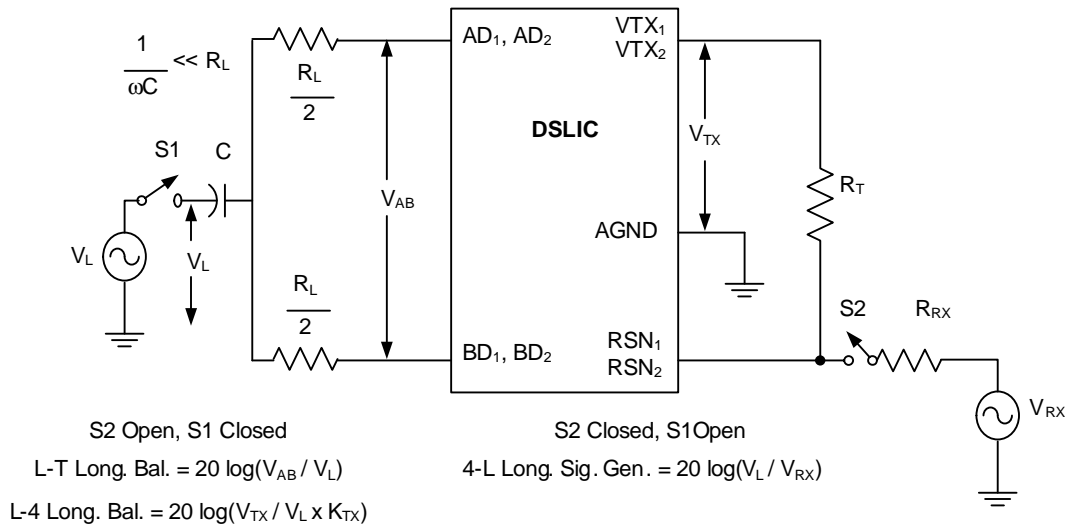


Figure 5. Two-Wire Return Loss Test Circuit

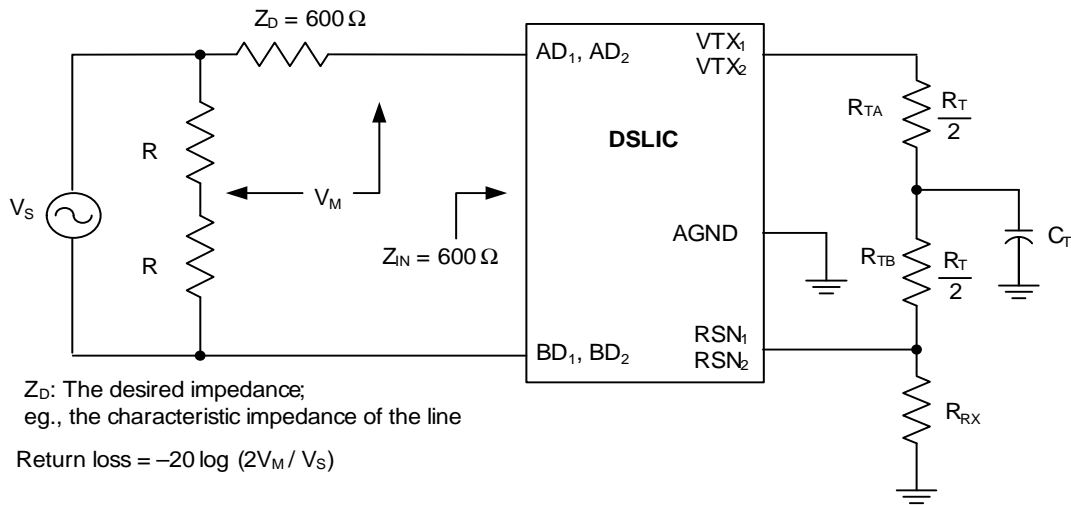


Figure 6. RFI Test Circuit

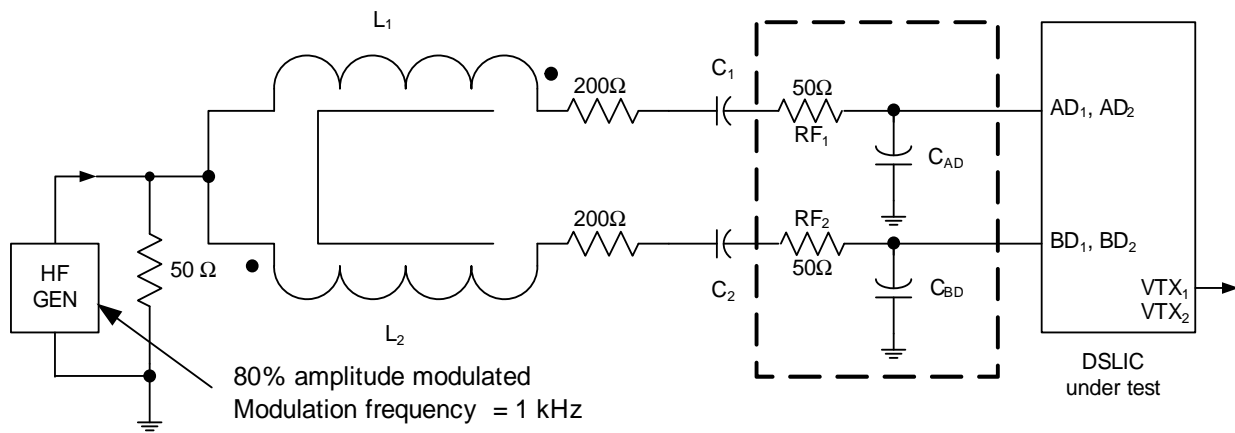
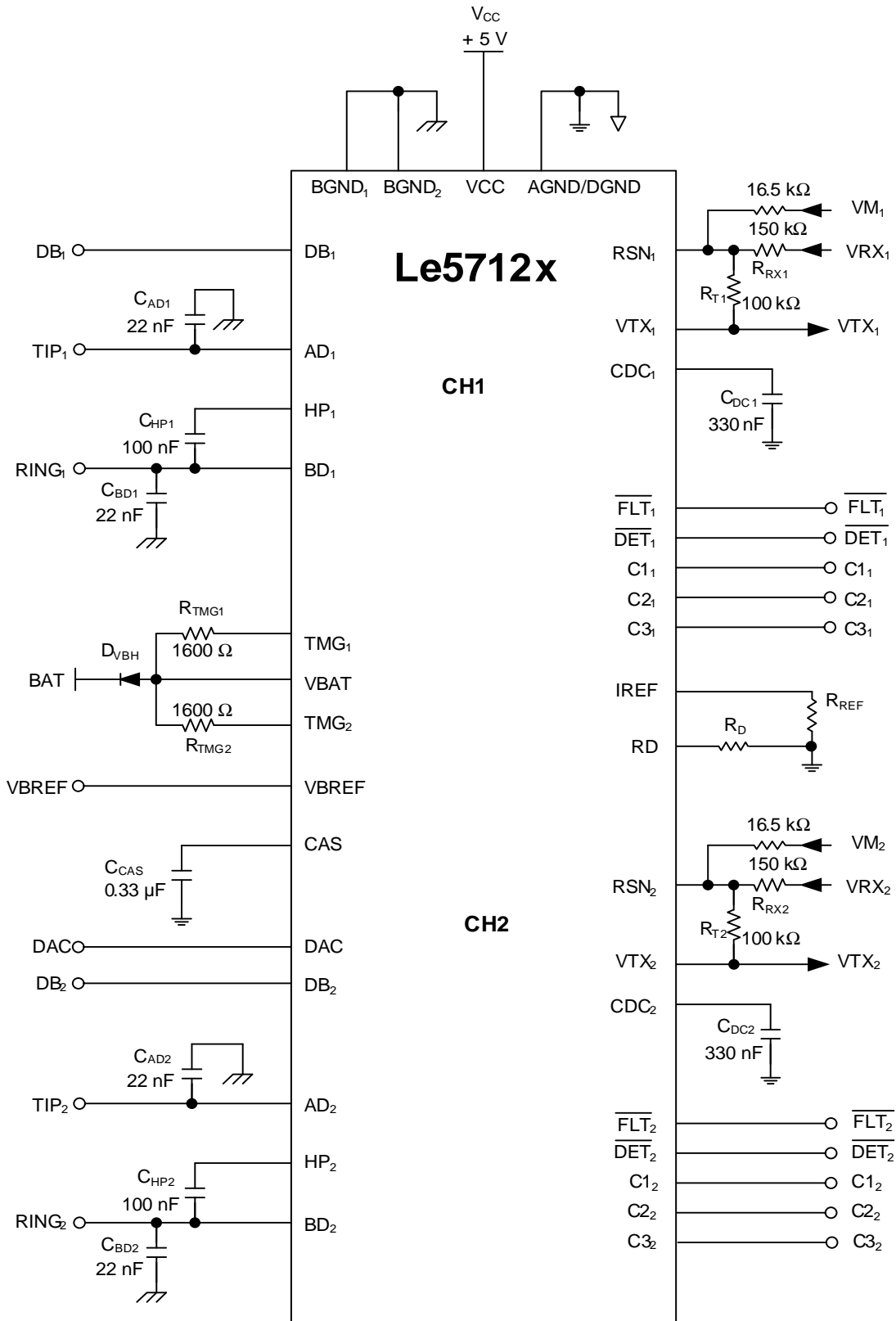


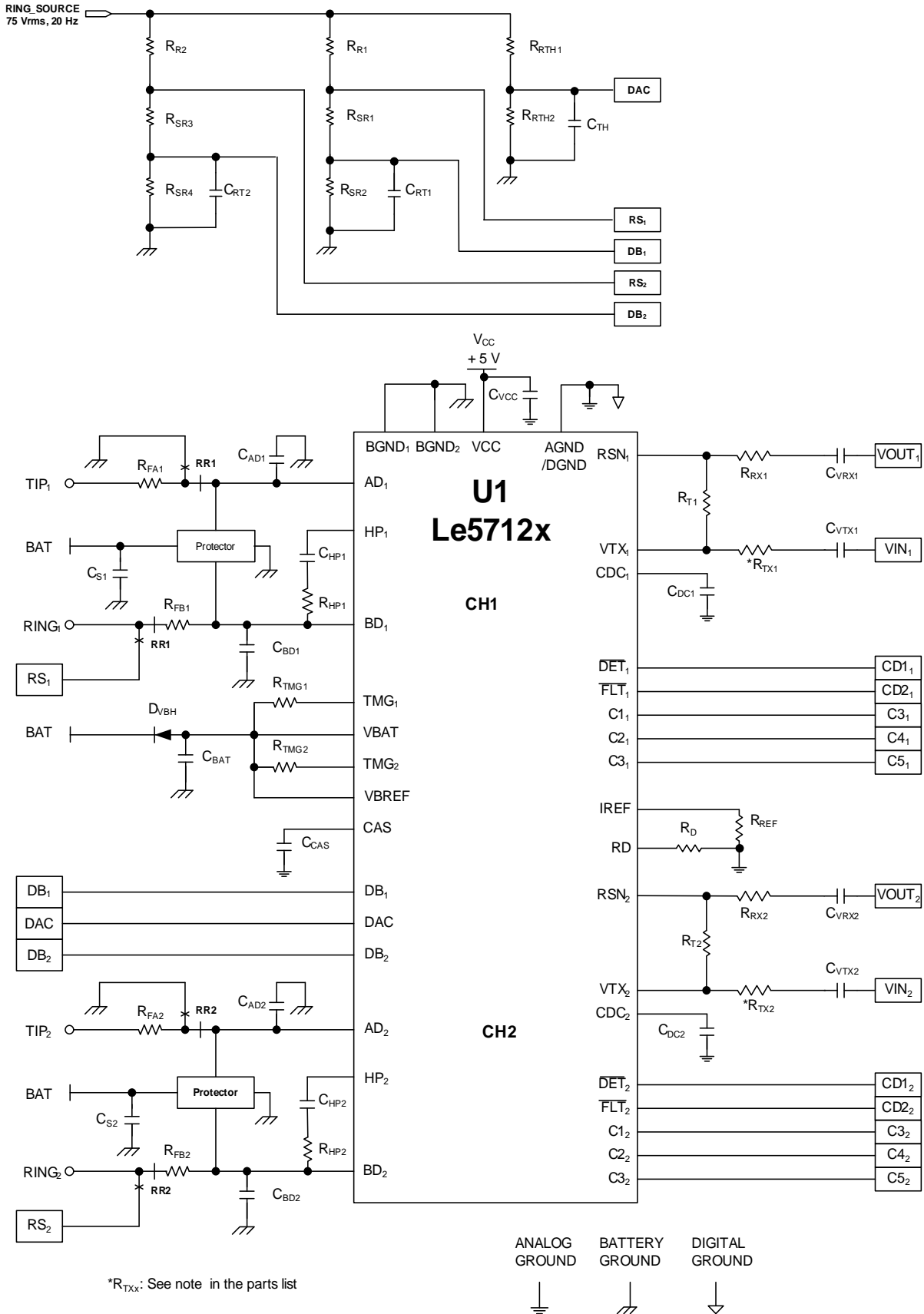


Figure 7. Le5712 Test Circuit



### POTS APPLICATION CIRCUIT (POTS WITH NO METERING)

For use with a Quad or Octal SLAC device; battery-backed ringing.



**APPLICATION CIRCUIT PARTS LIST (POTS WITH NO METERING)**

The following list defines the parts and part values required to meet target specification limits for channel i of the line card (i = 1,2).

Item	Quantity	Type	Value	Tol.	Rating	Note
<b>Ring and Ring Trip Sensing</b>						
R <sub>RTH1</sub>	1	SMT	1 MΩ	1%	1/16 W	
R <sub>SR1</sub> , R <sub>SR3</sub>	2	SMT	1.82 MΩ	1%	1/16 W	
R <sub>SR2</sub> , R <sub>SR4</sub>	2	SMT	2 MΩ	1%	1/16 W	
R <sub>RTH2</sub>	1	SMT	909 kΩ	1%	1/16 W	
R <sub>R1</sub> , R <sub>R2</sub>	2	Resistor Hybrid	400 Ω	5%	2 W	
C <sub>TH</sub>	1	Capacitor (X7R)	0.1 μF	20%	50 V	
C <sub>RT1</sub> , C <sub>RT2</sub>	2	Capacitor (X7R)	0.047 μF	20%	50 V	
<b>Fault Protection and Power Supplies</b>						
R <sub>FA1</sub> , R <sub>FB1</sub> , R <sub>FA2A</sub> , R <sub>FB2</sub>	4	Resistor Hybrid or PTC	50 Ω	1%		
Protector	1 or 2	Battery referenced thyristor				1
C <sub>S1</sub> , C <sub>S2</sub>	1 or 2	Capacitor (X7R)	0.1 μF	20%	100 V	2
C <sub>BAT</sub>	1	Capacitor (X7R)	0.1 μF	20%	100 V	
C <sub>VCC</sub>	1	Capacitor (X7R)	0.1 μF	20%	10 V	
D <sub>VBH</sub>	1	MURS 120 (D0-41) DIODE				3
R <sub>TMG1</sub> , R <sub>TMG2</sub>	2	SMT	1.8 kΩ	5%	1 W	4
<b>Other Components</b>						
R <sub>REF</sub>	1	SMT	14.3 kΩ	1%	1/16 W	5
R <sub>D</sub>	1	SMT	82.5 kΩ	1%	1/16 W	6
R <sub>HP1</sub> , R <sub>HP2</sub>	2	SMT	15.0 kΩ	1%	1/16 W	7
R <sub>T1</sub> , R <sub>T2</sub>	2	SMT	100 kΩ	1%	1/16 W	
R <sub>RX1</sub> , R <sub>RX2</sub>	2	SMT	75.0 kΩ	1%	1/16 W	
C <sub>AD1</sub> , C <sub>BD1</sub> , C <sub>AD2</sub> , C <sub>BD2</sub>	4	Capacitor (X7R)	0.022 μF	20%	100 V	
C <sub>HP1</sub> , C <sub>HP2</sub>	2	Capacitor (X7R)	0.1 μF	20%	100 V	
C <sub>VTX1</sub> , C <sub>VTX2</sub>	2	Capacitor (X7R)	0.01 μF	20%	10 V	
C <sub>VRX1</sub> , C <sub>VRX2</sub>	2	Capacitor (X7R)	0.1 μF	20%	10 V	
C <sub>DC1</sub> , C <sub>DC2</sub>	2	Capacitor (X7R)	0.33 μF	20%	5 V	
C <sub>CAS</sub>	1	Capacitor (X7R)	0.33 μF	20%	100 V	
R <sub>TX1</sub> , R <sub>TX2</sub>	2	SMT	2.00 kΩ	1%	1/16 W	8
U1	1	Le5712x				

**Notes:**

1. In case of single, one for each channel. In case of dual, one for one Le5712 Dual SLIC.
2. Consult protector vendor for recommended value. One for one protector device.
3. A Schottky diode with a voltage drop of 0.4V is desirable if Tip to battery fault is concerned.
4. Value was chosen to use resistor with 5% tolerance and 1 W rating. See "Thermal Management for the Le5711 and Le5712 Dual SLIC Device" for further details.
5. Sets the current limit at 33 mA.
6. Sets an off-hook detection threshold of 11 mA.
7. RHP will enhance dial pulse crosstalk performance. RHP being 15 k will make G24 from being 1/3 to 1/3.0841. RHB should be present in WinSLAC™ simulations.
8. R<sub>TX</sub> is optional and is required if C<sub>VTX</sub> is greater than 0.01μF.



**APPLICATION CIRCUIT PARTS LIST (POTS WITH METERING)**

The following list defines the parts and part values required to meet target specification limits for channel *i* of the line card (*i* = 1,2).

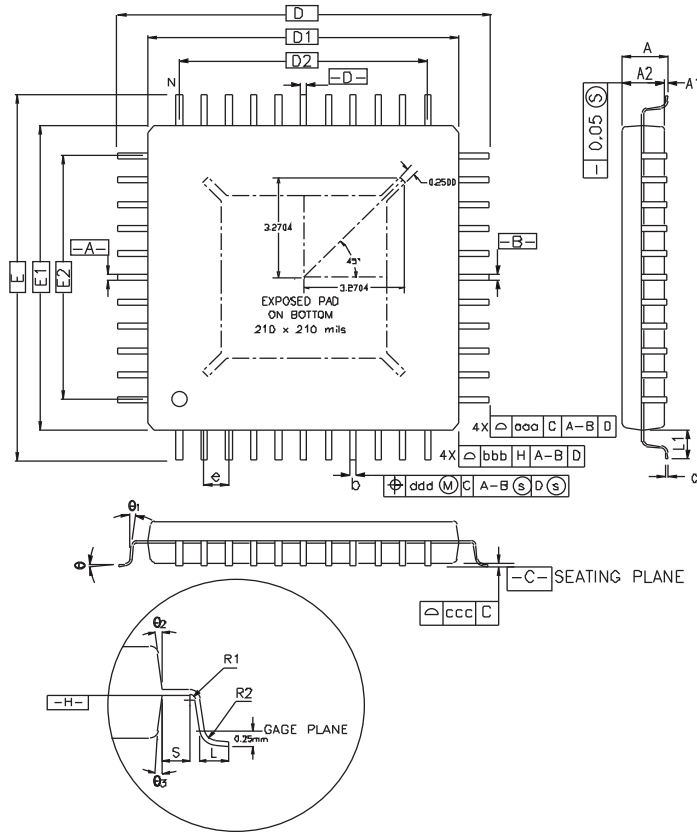
Item	Quantity	Type	Value	Tol.	Rating	Note
<b>Ringing and Ring Trip Sensing</b>						
R <sub>RTH1</sub>	1	SMT	1 MΩ	1%	1/16 W	
R <sub>SR1</sub> , R <sub>SR3</sub>	2	SMT	1.82 MΩ	1%	1/16 W	
R <sub>SR2</sub> , R <sub>SR4</sub>	2	SMT	2 MΩ	1%	1/16 W	
R <sub>RTH2</sub>	1	SMT	909 kΩ	1%	1/16 W	
R <sub>R1</sub> , R <sub>R2</sub>	2	Resistor Hybrid	400 Ω	5%	2 W	
C <sub>TH</sub>	1	Capacitor (X7R)	0.1 μF	20%	50 V	
C <sub>RT1</sub> , C <sub>RT2</sub>	2	Capacitor (X7R)	0.047 μF	20%	50 V	
<b>Fault Protection and Power Supplies</b>						
R <sub>FA1</sub> , R <sub>FB1</sub> , R <sub>FA2A</sub> , R <sub>FB2</sub>	4	Resistor Hybrid or PTC	50 Ω	1%		
Protector	1 or 2	Battery referenced thyristor				1
C <sub>S1</sub> , C <sub>S2</sub>	1 or 2	Capacitor (X7R)	0.1 μF	20%	100 V	2
C <sub>BAT</sub>	1	Capacitor (X7R)	0.1 μF	20%	100 V	
C <sub>VCC</sub>	1	Capacitor (X7R)	0.1 μF	20%	10 V	
D <sub>VBH</sub>	1	MURS 120 (D0-41) DIODE				3
R <sub>TMG1</sub> , R <sub>TMG2</sub>	2	SMT	1.8 kΩ	5%	1 W	4
<b>Components specific to Metering application circuit</b>						
C <sub>M1</sub> , C <sub>M2</sub>	2	Capacitor (X7R)	0.01 μF	20%	10 V	
C <sub>T1</sub> , C <sub>T2</sub>	2	Capacitor (X7R)	1000 pF	10%	10 V	
C <sub>X1</sub> , C <sub>X2</sub>	2	Capacitor (X7R)	1500 pF	10%	10 V	
C <sub>P1</sub> , C <sub>P2</sub>	2	Capacitor (X7R)	390 pF	10%	10 V	
C <sub>DET1</sub> , C <sub>DET2</sub>	2	Capacitor (X7R)	0.022 μF	20%	10V	
R <sub>M1</sub> , R <sub>M2</sub>	2	SMT	16.5 kΩ	1%	1/16 W	5
R <sub>TA1</sub> , R <sub>TA2</sub> , R <sub>TB1</sub> , R <sub>TB2</sub>	4	SMT	49.9 kΩ	1%	1/16 W	
R <sub>RX1</sub> , R <sub>RX2</sub>	2	SMT	71.5 kΩ	1%	1/16 W	
R <sub>P1</sub> , R <sub>P2</sub>	2	SMT	22.1 kΩ	1%	1/16 W	
R <sub>X1</sub> , R <sub>X2</sub>	2	SMT	4.99 kΩ	1%	1/16 W	
<b>Other Components</b>						
R <sub>REF</sub>	1	SMT	14.3 kΩ	1%	1/16 W	6
R <sub>D</sub>	1	SMT	82.5 kΩ	1%	1/16 W	7
R <sub>HP1</sub> , R <sub>HP2</sub>	2	SMT	15.0 kΩ	1%	1/16 W	8
C <sub>AD1</sub> , C <sub>BD1</sub> , C <sub>AD2</sub> , C <sub>BD2</sub>	4	Capacitor (X7R)	0.022 μF	20%	100 V	
C <sub>HP1</sub> , C <sub>HP2</sub>	2	Capacitor (X7R)	0.1 μF	20%	100 V	
C <sub>VTX1</sub> , C <sub>VTX2</sub>	2	Capacitor (X7R)	0.1 μF	20%	10 V	
C <sub>VRX1</sub> , C <sub>VRX2</sub>	2	Capacitor (X7R)	0.1 μF	20%	10 V	
C <sub>DC1</sub> , C <sub>DC2</sub>	2	Capacitor (X7R)	0.33 μF	20%	5 V	
C <sub>CAS</sub>	1	Capacitor (X7R)	0.33 μF	20%	100 V	
U1	1	Le5712x				

**Notes:**

- In case of single, one for each channel. In case of dual, one for one Le5712 Dual SLIC.
- Consult protector vendor for recommended value. One for one protector device.
- A Schottky diode with a voltage drop of 0.4V is desirable if Tip to battery fault is concerned.
- Value was chosen to use resistor with 5% tolerance and 1 W rating. See "Thermal Management for the Le5711 and Le5712 Dual SLIC Device" for further details.
- Sets a gain of about 5.5 dB into a load of 200 Ω at tip-ring ( $20\text{LOG}(200/16.5/1000*500/(1+500/3.0841*(200+100)/22.1/1000))$ ).
- Sets the current limit at 33 mA.
- Sets an off-hook detection threshold of 11 mA.
- RHP will enhance dial pulse crosstalk performance. RHP being 15 k will make G24 from being 1/3 to 1/3.0841. RHB should be present in WinSLAC™ simulations.

PHYSICAL DIMENSIONS

44-Pin eTQFP



Symbol	Min	Nom	Max
A	-	-	1.20
A1	0.05	-	0.15
A2	0.95	1.00	1.05
D	12 BSC		
D1	10 BSC		
E	12 BSC		
E1	10 BSC		
R2	0.08	-	0.20
R1	0.08	-	-
θ	0 deg	3.5 deg	7 deg
θ 1	0 deg	-	-
θ 2	11 deg	12 deg	13 deg
θ 3	11 deg	12 deg	13 deg

Symbol	Min	Nom	Max
c	0.09	-	0.20
L	0.45	0.60	0.75
L1	1.00 REF		
S	0.20	-	-
b	0.17	0.20	0.27
e	0.80 BSC		
D2	8.00		
E2	8.00		
aaa	0.20		
bbb	0.20		
ccc	0.10		
ddd	0.20		
N	44		

Notes:

- Controlling dimension in millimeter unless otherwise specified.
- Dimensions "D1" and "E1" do not include mold protrusion. Allowable protrusion is 0.25mm per side.  
"D1" and "E1" are maximum plastic body size dimensions including mold mismatch.
- Dimension "b" does not include Dambar protrusion. Allowable Dambar protrusion shall not cause the lead width to exceed the maximum "b" dimension by more than 0.08mm.
- Dambar can not be located on the lower radius or the foot. Minimum space between protrusion and an adjacent lead is 0.07mm for 0.4mm and 0.5mm pitch packages.
- Square dotted line is E-Pad outline.
- "N" is the total number of terminals.

44-Pin eTQFP

Note:

Packages may have mold tooling markings on the surface. These markings have no impact on the form, fit or function of the device. Markings will vary with the mold tool used in manufacturing.

## REVISION HISTORY

### Revision C1 to D1

- [Page 9](#), *Supply Currents and Power Dissipation*, (On-hook), regarding disconnect operational state,  $I_{VBAT}$  max from 0.7mA to 0.8mA; SLIC Device Power max from 50mW to 62mW.
- In *Device Specifications*, page 11,  $I_{GSD}$ , Ground Start Detection Threshold, changed max from 15.2mA to 16.0mA.
- In *Device Specifications*, page 11,  $I_{FAULT}$ , changed max from 18mA to 20mA.
- In *Device Specifications*, page 11,  $I_{IH}$ , Input High Current of C1/2/3, changed max from 40 $\mu$ A to 90 $\mu$ A, min from -100 $\mu$ A to -110  $\mu$ A, with test condition to be  $V_{IH}=2.0V$ .
- In *Device Specifications*, page 11,  $I_{IL}$ , Input Low Current of C1/2/3, changed test condition to be  $V_{IL}=0.8V$ .

### Revision D1 to E1

- Added green package OPNs to [Ordering Information, on page 1](#)
- Added [Package Assembly, on page 8](#)

### Revision E1 to F1

- Removed Le57D123 and Le57D124 devices from [Ordering Information, on page 1](#). Removed descriptions related to Le57D123 and Le57D124, such as old note 2 on page 12. The notes on page 12 are re-arranged that are applicable to page 9, page 10, and page 11.
- Removed non-green OPNs from [Ordering Information, on page 1](#).
- Modified descriptions regarding FLTs in Pin Descriptions, on page 7.
- Updated and added note about package marking in [Physical Dimensions, on page 22](#).
- Separated parts list for with and without metering applications, on page 19 and 21.

### Revision F1 to G1

- Added Note 1 to [Pin Descriptions, on page 7](#).
- Rearranged notes on page 12 and applicable notes in tables on pages 9, 10, and 11.
- Added [Application Circuit Parts List \(Pots with no metering\), on page 19](#).
- Modified [Application Circuit Parts List \(Pots with metering\), on page 21](#)".

### Revision G1 to G2

- Added new headers/footers due to Zarlink purchase of Legerity on August 3, 2007

### Revision G2 (version 7) to Version 8

- Data sheet format changed to new Microsemi format.
- Updated specifications to reflect "Le5712 Dual SLIC Device Revision CAA" errata, September 10, 2004. This version of the data sheet, version 8, is consistent ant with the actual performance of the silicon. There is no active errata.
  - Device Specification Table on page 10 for Longitudinal Balance, Le57122, the first 4 lines. All numbers lowered by 3dB.
  - Device Specification Table on page 9 for VAB voltages, added "Active Reverse".
  - Device Specification Table on page 9 for VAB voltages, added "Metering Reverse".
  - Device Specification Table on page 9 for IL, Long Loops, Active state, RLDC=2000ohms, BAT=-48V, minimum spec to 19.8mA from 20mA.
  - Device Specification Table on page 11 for Fault Detector, the maximum is 22mA from 20mA.
  - Device Specification Table on page 11 for 2-to-4 gain, the maximum is -9.32dB from -9.34dB.
  - Device Specification Table on page 11 for 4-to-2 gain, the minimum is -0.20dB from -0.25dB.

Information relating to products and services furnished herein by Microsemi Corporation or its subsidiaries (collectively "Microsemi") is believed to be reliable. However, Microsemi assumes no liability for errors that may appear in this publication, or for liability otherwise arising from the application or use of any such information, product or service or for any infringement of patents or other intellectual property rights owned by third parties which may result from such application or use. Neither the supply of such information or purchase of product or service conveys any license, either express or implied, under patents or other intellectual property rights owned by Microsemi or licensed from third parties by Microsemi, whatsoever. Purchasers of products are also hereby notified that the use of product in certain ways or in combination with Microsemi, or non-Microsemi furnished goods or services may infringe patents or other intellectual property rights owned by Microsemi.

This publication is issued to provide information only and (unless agreed by Microsemi in writing) may not be used, applied or reproduced for any purpose nor form part of any order or contract nor to be regarded as a representation relating to the products or services concerned. The products, their specifications, services and other information appearing in this publication are subject to change by Microsemi without notice. No warranty or guarantee express or implied is made regarding the capability, performance or suitability of any product or service. Information concerning possible methods of use is provided as a guide only and does not constitute any guarantee that such methods of use will be satisfactory in a specific piece of equipment. It is the user's responsibility to fully determine the performance and suitability of any equipment using such information and to ensure that any publication or data used is up to date and has not been superseded. Manufacturing does not necessarily include testing of all functions or parameters. These products are not suitable for use in any medical and other products whose failure to perform may result in significant injury or death to the user. All products and materials are sold and services provided subject to Microsemi's conditions of sale which are available on request.

**For more information about all Microsemi products  
visit our website at  
[www.microsemi.com](http://www.microsemi.com)**

TECHNICAL DOCUMENTATION – NOT FOR RESALE



**Microsemi Corporate Headquarters**  
One Enterprise, Aliso Viejo CA 92656 USA  
Within the USA: +1 (949) 380-6100  
Sales: +1 (949) 380-6136  
Fax: +1 (949) 215-4996

Microsemi Corporation (NASDAQ: MSCC) offers a comprehensive portfolio of semiconductor solutions for: aerospace, defense and security; enterprise and communications; and industrial and alternative energy markets. Products include high-performance, high-reliability analog and RF devices, mixed signal and RF integrated circuits, customizable SoCs, FPGAs, and complete subsystems. Microsemi is headquartered in Aliso Viejo, Calif. Learn more at [www.microsemi.com](http://www.microsemi.com).

© 2013 Microsemi Corporation. All rights reserved. Microsemi and the Microsemi logo are trademarks of Microsemi Corporation. All other trademarks and service marks are the property of their respective owners.